

ABSTRACT

A memory and an electronic device are provided. The memory includes a plurality of bit line functional groups, a plurality of memory cells, a first staircase structure, and a second staircase structure located on a base substrate; the plurality of bit line function groups are spaced apart along a first direction perpendicular to the base substrate, each bit line function group includes a first bit line, a second bit line coupled to the first bit line, and a third bit line coupled to the first bit line, the first bit line extending along a second direction parallel to the base substrate, the second bit line and the third bit line extending along a third direction parallel to the base substrate, and the second direction intersecting with the third direction; the second bit line and the plurality of memory cells are located on one side of the first bit line in the third direction, the third bit line, the first staircase structure, and the second staircase structure are located on the other side of the first bit line in the third direction, and the first staircase structure and the second staircase structure are located on opposite sides of the third bit line in the second direction. The stack structure in the memory is compact, which is beneficial to increasing the number of dies that can be cut out from each wafer.

[Fig. 2A]